# Central \*\* Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N4001G THRU 1N4007G

1.0 AMP RECTIFIER GLASS PASSIVATED CHIP 50 THRU 1000 VOLTS

JEDEC DO-41 CASE

### DESCRIPTION

The CENTRAL SEMICONDUCTOR 1 ampere axial lead epoxy silicon rectifier is a high quality, well constructed, highly reliable component designed for use in all types of commercial, industrial, entertainment, computer, and automotive applications. Because of its superior electrical characteristics, this rectifier family is used as a universal replacement for many other rectifiers. This series of devices is manufactured by the planar process using the glass passivation technique.

## **FEATURES**

- •1 amp at 100°C
- compression molded epoxy
- •superior solvent resistance

- •50 amps surge current
- reliable internal construction
- •glass passivated chip for high reliability

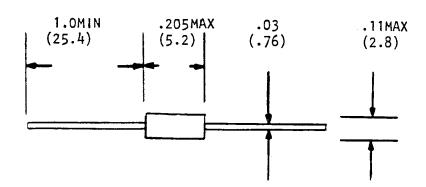
# MAXIMUM RATINGS (TA=25°C)

SYMBOL	1N4001G	1N4002G	1N4003G	1N4004G	1N4005G	1N4006G	1N4007G	UNIT
VRRM	50	100	200	400	600	800	1000	V
VR (RMS)	35	70	140	280	420	560	700	٧
10				1.0				Α
IFSM TJ. TSTG				50				Α
•			-	65 to +175				°C
ELECTRICAL	CHARACTERIS	TICS (TA=	=25°C)					

LLLOTRICAL	CHARACTERISTICS	(IA=25 C)
SYMBOL	TEST CONDITIONS	

STITIBUL	TEST CONDITIONS	MIN	MAX	UNIT
٧ <sub>F</sub>	I F=1.0A		1.1	
1 <sub>R</sub>	$V_R$ =Rated $V_{RRM}$		5.0	uА
I <sub>R</sub>	$V_{R}$ =Rated $V_{RRM}$ , $T_{A}$ =100°C		50	μA

#### OUTLINE DRAWING:



Dimensions in inches and (millimeters).